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October 2016

# FDPC3D5N025X9D

## PowerTrench® Power Clip 25V Symmetric Dual N-Channel MOSFET

### Features

Q1: N-Channel

■ Max  $r_{DS(on)}$  = 3.01 mΩ at  $V_{GS} = 10\text{ V}$ ,  $I_D = 18\text{ A}$ ■ Max  $r_{DS(on)}$  = 3.67 mΩ at  $V_{GS} = 4.5\text{ V}$ ,  $I_D = 16\text{ A}$ 

Q2: N-Channel

■ Max  $r_{DS(on)}$  = 3.01 mΩ at  $V_{GS} = 10\text{ V}$ ,  $I_D = 18\text{ A}$ ■ Max  $r_{DS(on)}$  = 3.67 mΩ at  $V_{GS} = 4.5\text{ V}$ ,  $I_D = 16\text{ A}$ 

■ Low Inductance Packaging Shortens Rise/Fall Times, Resulting in Lower Switching Losses

■ MOSFET Integration Enables Optimum Layout for Lower Circuit Inductance and Reduced Switch Node Ringing

■ RoHS Compliant

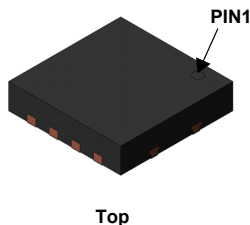


### General Description

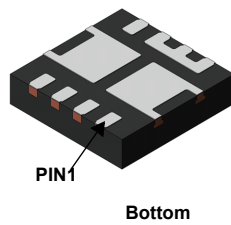
This device includes two specialized N-Channel MOSFETs in a dual package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q2) and synchronous (Q1) have been designed to provide optimal power efficiency.

### Applications

- Computing
- Communications
- General Purpose Point of Load

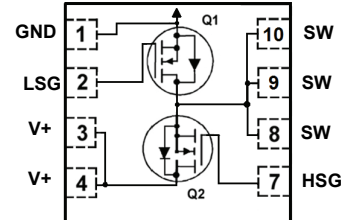
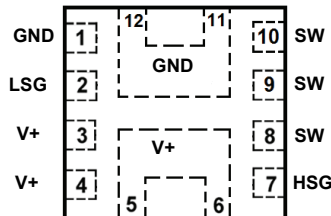


Top



Bottom

Power Clip 33 Symmetric



| Pin     | Name     | Description     | Pin     | Name    | Description     | Pin    | Name | Description                    |
|---------|----------|-----------------|---------|---------|-----------------|--------|------|--------------------------------|
| 1,11,12 | GND(LSS) | Low Side Source | 3,4,5,6 | V+(HSD) | High Side Drain | 8,9,10 | SW   | Switching Node, Low Side Drain |
| 2       | LSG      | Low Side Gate   | 7       | HSG     | High Side Gate  |        |      |                                |

### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted.

| Symbol         | Parameter                                                       | Q1                    | Q2                    | Units            |
|----------------|-----------------------------------------------------------------|-----------------------|-----------------------|------------------|
| $V_{DS}$       | Drain to Source Voltage                                         | 25                    | 25                    | V                |
| $V_{GS}$       | Gate to Source Voltage                                          | $\pm 12$              | $\pm 12$              | V                |
| $I_D$          | Drain Current -Continuous $T_C = 25^\circ\text{C}$ (Note5)      | 74                    | 74                    | A                |
|                | -Continuous $T_C = 100^\circ\text{C}$ (Note5)                   | 47                    | 47                    |                  |
|                | -Continuous $T_A = 25^\circ\text{C}$                            | 18 <sup>Note1a</sup>  | 18 <sup>Note1b</sup>  |                  |
|                | -Pulsed $T_A = 25^\circ\text{C}$ (Note 4)                       | 349                   | 349                   |                  |
| $E_{AS}$       | Single Pulse Avalanche Energy (Note 3)                          | 96                    | 96                    | mJ               |
| $P_D$          | Power Dissipation for Single Operation $T_C = 25^\circ\text{C}$ | 26                    | 26                    | W                |
|                | Power Dissipation for Single Operation $T_A = 25^\circ\text{C}$ | 1.8 <sup>Note1a</sup> | 1.8 <sup>Note1b</sup> |                  |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range                | -55 to +150           |                       | $^\circ\text{C}$ |

### Thermal Characteristics

|                 |                                         |                       |                       |                    |
|-----------------|-----------------------------------------|-----------------------|-----------------------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 4.8                   | 4.8                   | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 70 <sup>Note1a</sup>  | 70 <sup>Note1b</sup>  |                    |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 135 <sup>Note1c</sup> | 135 <sup>Note1d</sup> |                    |

## Package Marking and Ordering Information

| Device Marking | Device         | Package            | Reel Size | Tape Width | Quantity   |
|----------------|----------------|--------------------|-----------|------------|------------|
| FDPCN025X9D    | FDPC3D5N025X9D | Power Clip 33 Symm | 13 "      | 12 mm      | 3000 units |

Electrical Characteristics  $T_J = 25^\circ\text{C}$  unless otherwise noted.

| Symbol | Parameter | Test Conditions | Type | Min. | Typ. | Max. | Units |
|--------|-----------|-----------------|------|------|------|------|-------|
|--------|-----------|-----------------|------|------|------|------|-------|

## Off Characteristics

|                                      |                                           |                                                                                                                                |          |          |          |                        |                                |
|--------------------------------------|-------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------|----------|----------|----------|------------------------|--------------------------------|
| $BV_{DSS}$                           | Drain to Source Breakdown Voltage         | $I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$<br>$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$                         | Q1<br>Q2 | 25<br>25 |          |                        | V                              |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$<br>$I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$     | Q1<br>Q2 |          | 23<br>23 |                        | mV/ $^\circ\text{C}$           |
| $I_{DSS}$                            | Zero Gate Voltage Drain Current           | $V_{DS} = 20\ \text{V}$ , $V_{GS} = 0\ \text{V}$<br>$V_{DS} = 20\ \text{V}$ , $V_{GS} = 0\ \text{V}$                           | Q1<br>Q2 |          |          | 1<br>1                 | $\mu\text{A}$<br>$\mu\text{A}$ |
| $I_{GSS}$                            | Gate to Source Leakage Current, Forward   | $V_{GS} = 12\ \text{V}/-8\ \text{V}$ , $V_{DS} = 0\ \text{V}$<br>$V_{GS} = 12\ \text{V}/-8\ \text{V}$ , $V_{DS} = 0\ \text{V}$ | Q1<br>Q2 |          |          | $\pm 100$<br>$\pm 100$ | nA<br>nA                       |

## On Characteristics

|                                        |                                                          |                                                                                                                                                                                 |          |            |                    |                      |                      |
|----------------------------------------|----------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------|------------|--------------------|----------------------|----------------------|
| $V_{GS(th)}$                           | Gate to Source Threshold Voltage                         | $V_{GS} = V_{DS}$ , $I_D = 250\ \mu\text{A}$<br>$V_{GS} = V_{DS}$ , $I_D = 250\ \mu\text{A}$                                                                                    | Q1<br>Q2 | 1.0<br>1.0 | 1.5<br>1.5         | 3.0<br>3.0           | V                    |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$<br>$I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$                                                      | Q1<br>Q2 |            | -4<br>-4           |                      | mV/ $^\circ\text{C}$ |
| $r_{DS(on)}$                           | Drain to Source On Resistance                            | $V_{GS} = 10\ \text{V}$ , $I_D = 18\ \text{A}$<br>$V_{GS} = 4.5\ \text{V}$ , $I_D = 16\ \text{A}$<br>$V_{GS} = 10\ \text{V}$ , $I_D = 18\ \text{A}$ , $T_J = 125^\circ\text{C}$ | Q1       |            | 2.0<br>2.4<br>2.87 | 3.01<br>3.67<br>4.32 | m $\Omega$           |
|                                        |                                                          | $V_{GS} = 10\ \text{V}$ , $I_D = 18\ \text{A}$<br>$V_{GS} = 4.5\ \text{V}$ , $I_D = 16\ \text{A}$<br>$V_{GS} = 10\ \text{V}$ , $I_D = 18\ \text{A}$ , $T_J = 125^\circ\text{C}$ | Q2       |            | 2.5<br>2.9<br>3.6  | 3.01<br>3.67<br>4.33 |                      |
| $g_{FS}$                               | Forward Transconductance                                 | $V_{DS} = 5\ \text{V}$ , $I_D = 18\ \text{A}$<br>$V_{DS} = 5\ \text{V}$ , $I_D = 18\ \text{A}$                                                                                  | Q1<br>Q2 |            | 133<br>124         |                      | S                    |

## Dynamic Characteristics

|           |                              |                                                                               |          |            |              |              |          |
|-----------|------------------------------|-------------------------------------------------------------------------------|----------|------------|--------------|--------------|----------|
| $C_{iss}$ | Input Capacitance            | Q1:<br>Q2:                                                                    | Q1<br>Q2 |            | 2385<br>2385 | 3340<br>3340 | pF       |
| $C_{oss}$ | Output Capacitance           | $V_{DS} = 13\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$        | Q1<br>Q2 |            | 612<br>612   | 860<br>860   | pF       |
| $C_{rss}$ | Reverse Transfer Capacitance | Q2:<br>$V_{DS} = 13\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$ | Q1<br>Q2 |            | 78<br>78     | 130<br>130   | pF       |
| $R_g$     | Gate Resistance              |                                                                               | Q1<br>Q2 | 0.1<br>0.1 | 0.6<br>0.6   | 1.8<br>1.8   | $\Omega$ |

## Switching Characteristics

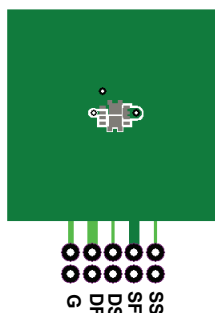
|              |                               |                                                                                                              |          |  |            |          |    |
|--------------|-------------------------------|--------------------------------------------------------------------------------------------------------------|----------|--|------------|----------|----|
| $t_{d(on)}$  | Turn-On Delay Time            | Q1:<br>$V_{DD} = 13\ \text{V}$ , $I_D = 18\ \text{A}$ , $R_{GEN} = 6\ \Omega$                                | Q1<br>Q2 |  | 10<br>10   | 20<br>20 | ns |
| $t_r$        | Rise Time                     |                                                                                                              | Q1<br>Q2 |  | 3<br>3     | 10<br>10 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time           | Q2:<br>$V_{DD} = 13\ \text{V}$ , $I_D = 18\ \text{A}$ , $R_{GEN} = 6\ \Omega$                                | Q1<br>Q2 |  | 29<br>29   | 46<br>46 | ns |
| $t_f$        | Fall Time                     |                                                                                                              | Q1<br>Q2 |  | 3<br>3     | 10<br>10 | ns |
| $Q_g$        | Total Gate Charge             | $V_{GS} = 0\ \text{V}$ to $10\ \text{V}$                                                                     | Q1<br>Q2 |  | 36<br>36   | 51<br>51 | nC |
| $Q_g$        | Total Gate Charge             | $V_{GS} = 0\ \text{V}$ to $4.5\ \text{V}$                                                                    | Q1<br>Q2 |  | 17<br>17   | 24<br>24 | nC |
| $Q_{gs}$     | Gate to Source Gate Charge    | Q1<br>$V_{DD} = 13\ \text{V}$ , $I_D = 18\ \text{A}$<br>Q2<br>$V_{DD} = 13\ \text{V}$ , $I_D = 18\ \text{A}$ | Q1<br>Q2 |  | 5.3<br>5.3 |          | nC |
| $Q_{gd}$     | Gate to Drain "Miller" Charge |                                                                                                              | Q1<br>Q2 |  | 3.9<br>3.9 |          | nC |

## Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

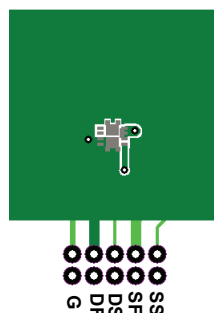
| Symbol                                    | Parameter                             | Test Conditions                                                                                              | Type     | Min. | Typ.       | Max.       | Units |
|-------------------------------------------|---------------------------------------|--------------------------------------------------------------------------------------------------------------|----------|------|------------|------------|-------|
| <b>Drain-Source Diode Characteristics</b> |                                       |                                                                                                              |          |      |            |            |       |
| $V_{SD}$                                  | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{ V}$ , $I_S = 18\text{ A}$ (Note 2)<br>$V_{GS} = 0\text{ V}$ , $I_S = 18\text{ A}$ (Note 2) | Q1<br>Q2 |      | 0.8<br>0.8 | 1.2<br>1.2 | V     |
| $I_S$                                     | Diode continuous forward current      | $T_C = 25\text{ }^{\circ}\text{C}$                                                                           | Q1<br>Q2 |      | 74<br>74   |            | A     |
| $I_{S,Pulse}$                             | Diode pulse current                   |                                                                                                              | Q1<br>Q2 |      | 349<br>349 |            | A     |
| $t_{rr}$                                  | Reverse Recovery Time                 | Q1<br>$I_F = 18\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$                                               | Q1<br>Q2 |      | 35<br>35   | 56<br>56   | ns    |
| $Q_{rr}$                                  | Reverse Recovery Charge               | Q2<br>$I_F = 18\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$                                               | Q1<br>Q2 |      | 19<br>19   | 35<br>35   | nC    |

Notes:

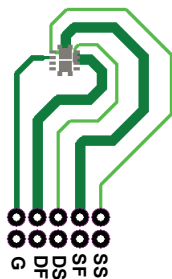
1.  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta CA}$  is determined by the user's board design.



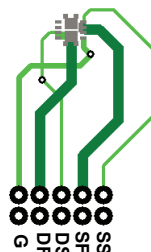
a. 70  $^{\circ}\text{C}/\text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b. 70  $^{\circ}\text{C}/\text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



c. 135  $^{\circ}\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper



d. 135  $^{\circ}\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.

3. Q1 :  $E_{AS}$  of 96 mJ is based on starting  $T_J = 25\text{ }^{\circ}\text{C}$ ; N-ch:  $L = 3\text{ mH}$ ,  $I_{AS} = 8\text{ A}$ ,  $V_{DD} = 25\text{ V}$ ,  $V_{GS} = 10\text{ V}$ . 100% test at  $L = 0.1\text{ mH}$ ,  $I_{AS} = 26\text{ A}$ .

Q2:  $E_{AS}$  of 96 mJ is based on starting  $T_J = 25\text{ }^{\circ}\text{C}$ ; N-ch:  $L = 3\text{ mH}$ ,  $I_{AS} = 8\text{ A}$ ,  $V_{DD} = 25\text{ V}$ ,  $V_{GS} = 10\text{ V}$ . 100% test at  $L = 0.1\text{ mH}$ ,  $I_{AS} = 26\text{ A}$ .

4. Pulse Id refers to Figure.11 & Figure. 26 Forward Bias Safe Operation Area.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

# Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

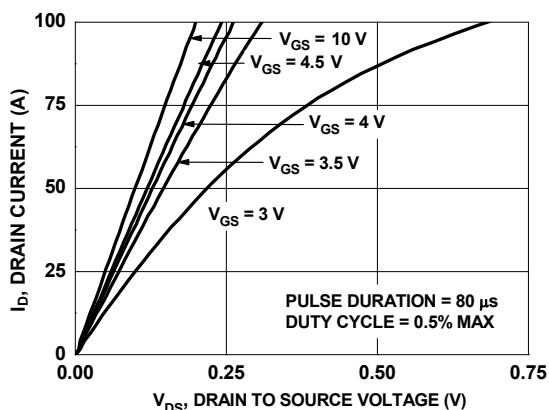


Figure 1. On Region Characteristics

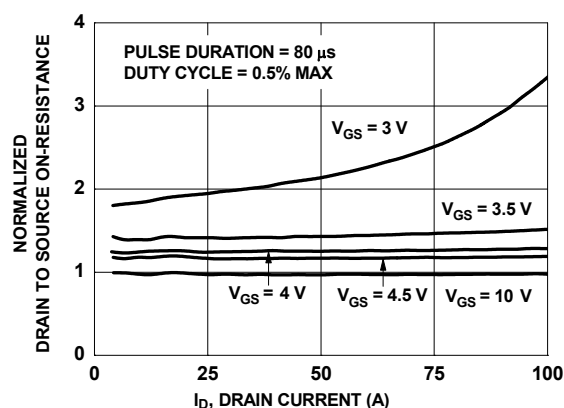


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

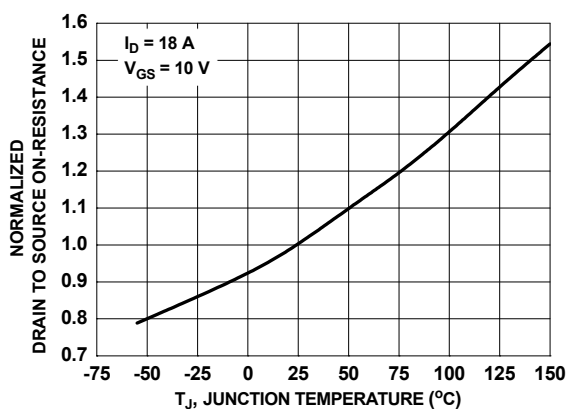


Figure 3. Normalized On Resistance vs. Junction Temperature

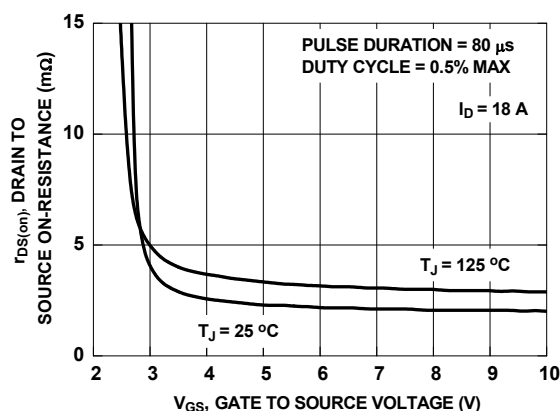


Figure 4. On-Resistance vs. Gate to Source Voltage

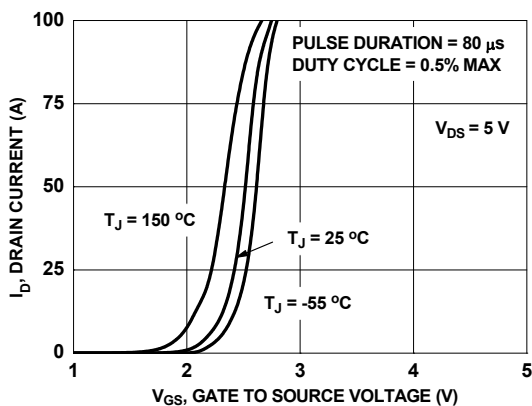


Figure 5. Transfer Characteristics

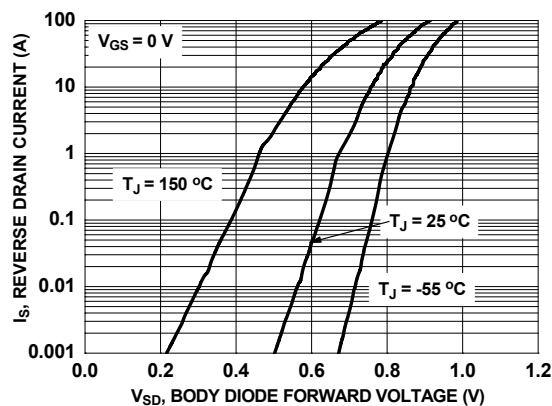


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

# Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

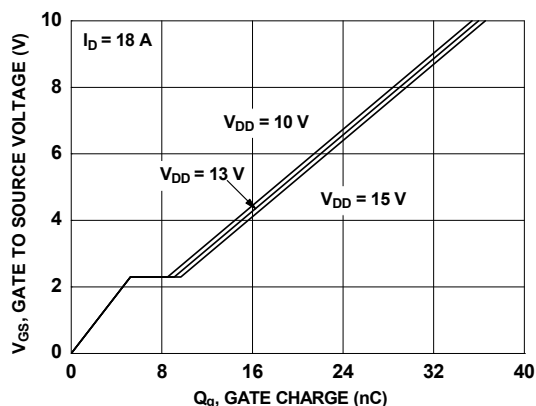


Figure 7. Gate Charge Characteristics

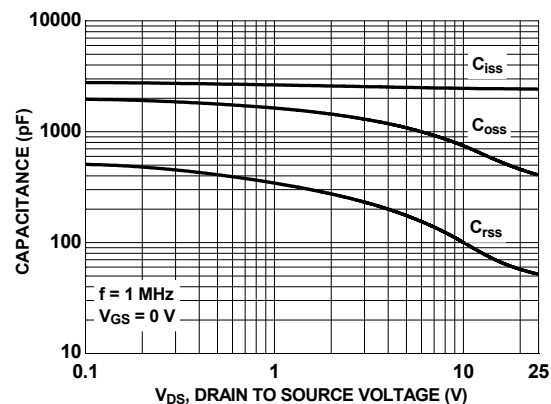


Figure 8. Capacitance vs. Drain to Source Voltage

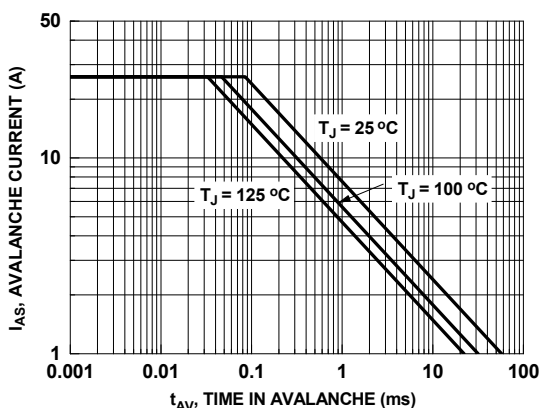


Figure 9. Unclamped Inductive Switching Capability

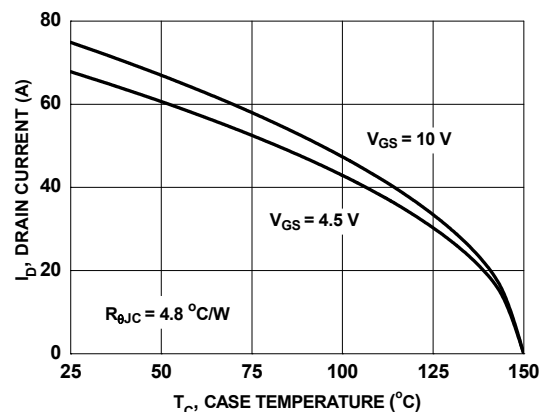


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

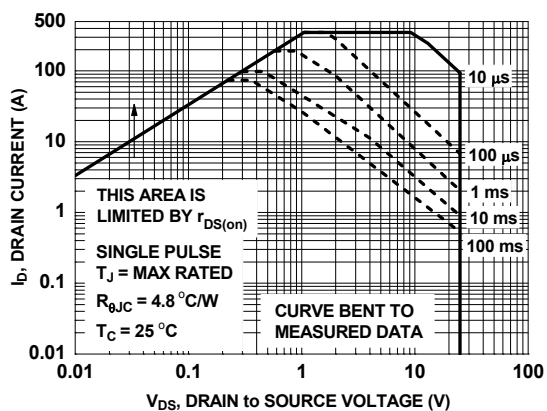


Figure 11. Forward Bias Safe Operating Area

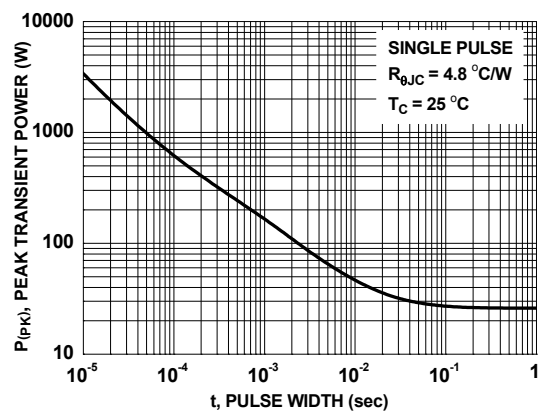
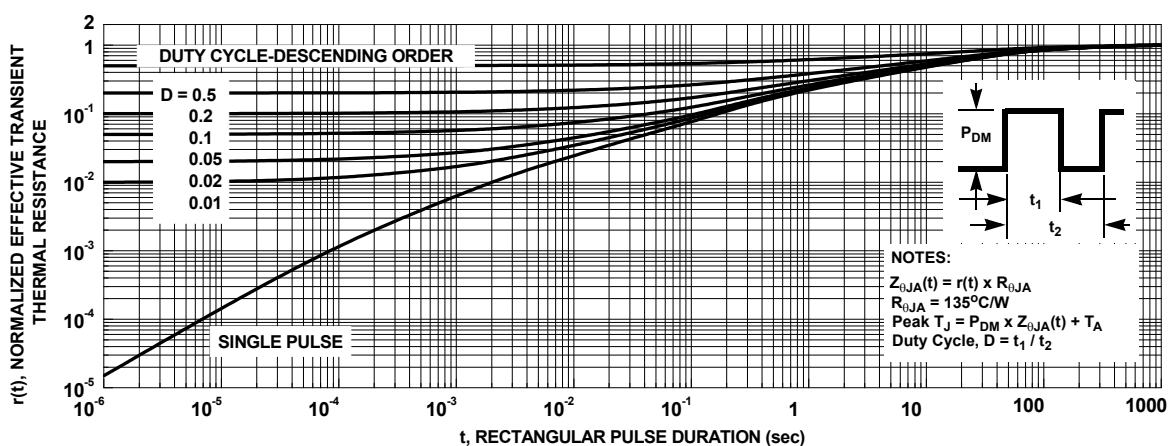
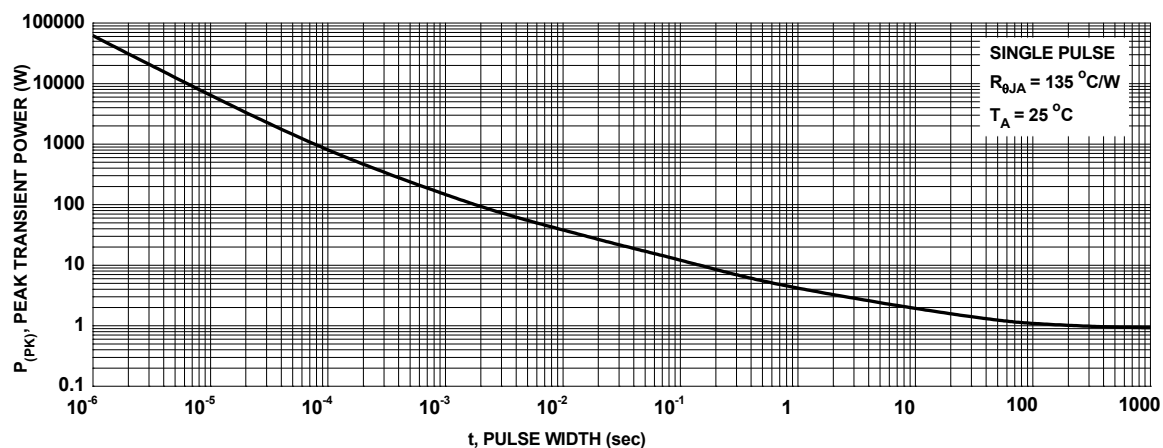
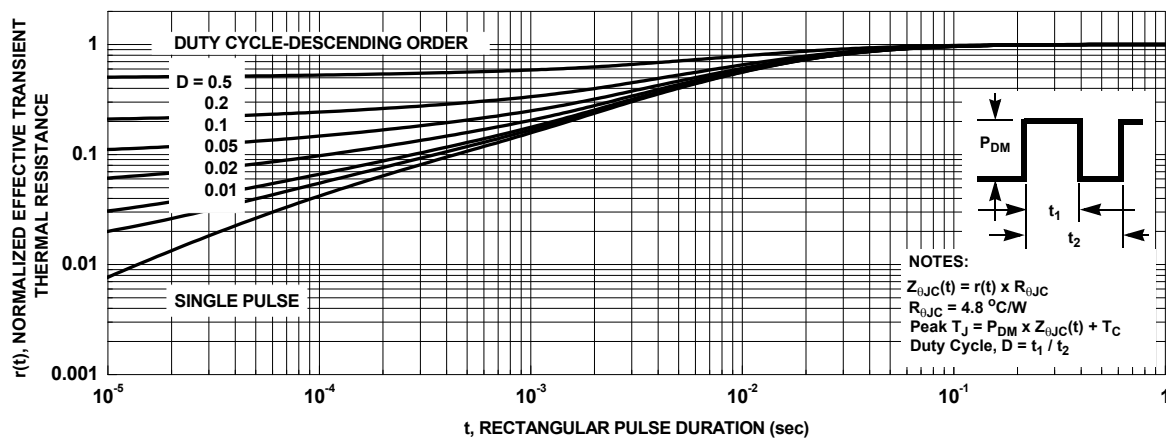


Figure 12. Single Pulse Maximum Power Dissipation

# Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.



# Typical Characteristics (Q2 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

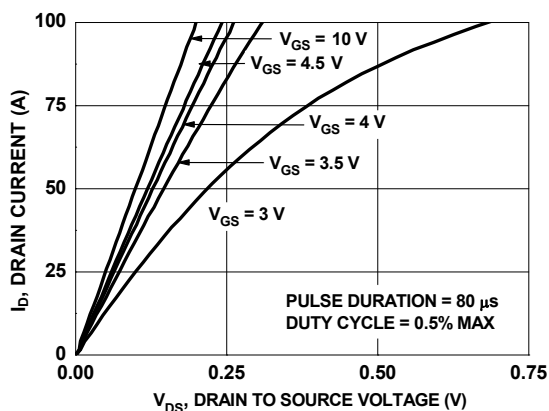


Figure 16. On-Region Characteristics

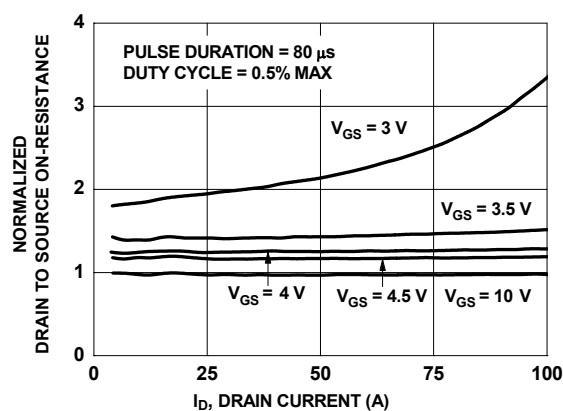


Figure 17. Normalized on-Resistance vs. Drain Current and Gate Voltage

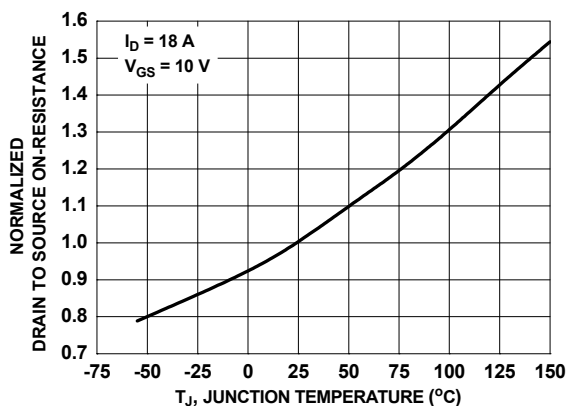


Figure 18. Normalized On-Resistance vs. Junction Temperature

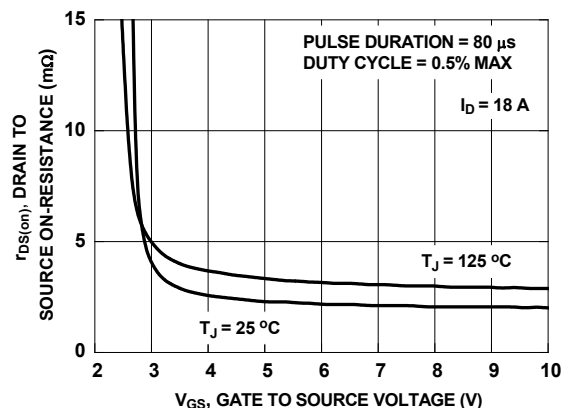


Figure 19. On-Resistance vs. Gate to Source Voltage

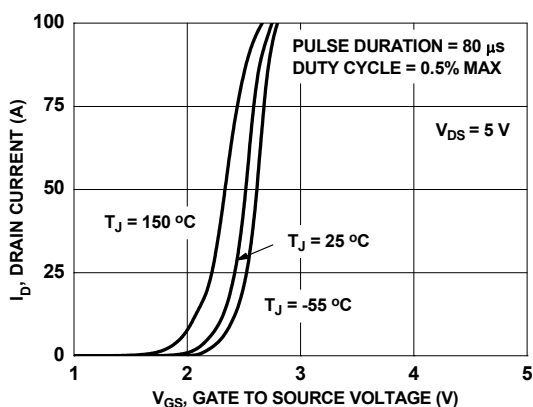


Figure 20. Transfer Characteristics

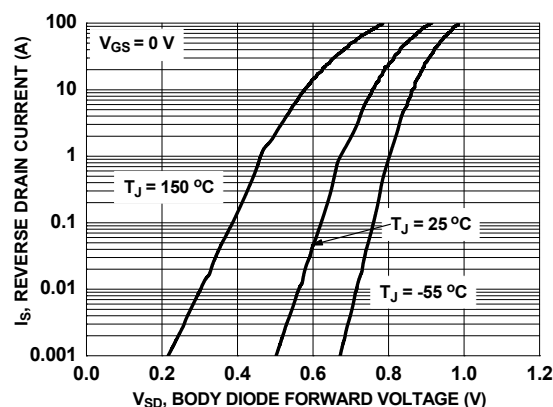


Figure 21. Source to Drain Diode Forward Voltage vs. Source Current

# Typical Characteristics (Q2 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

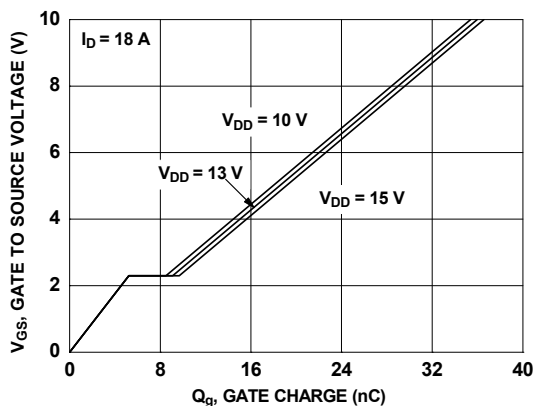


Figure 22. Gate Charge Characteristics

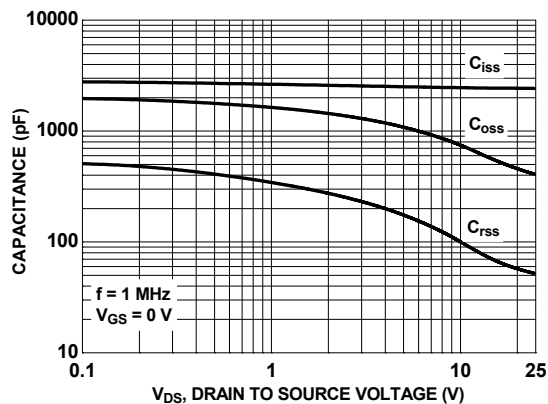


Figure 23. Capacitance vs. Drain to Source Voltage

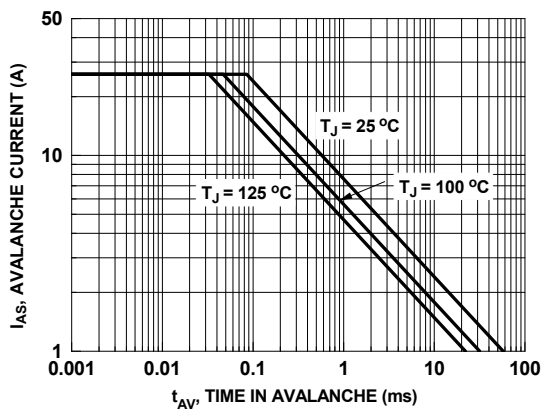


Figure 24. Unclamped Inductive Switching Capability

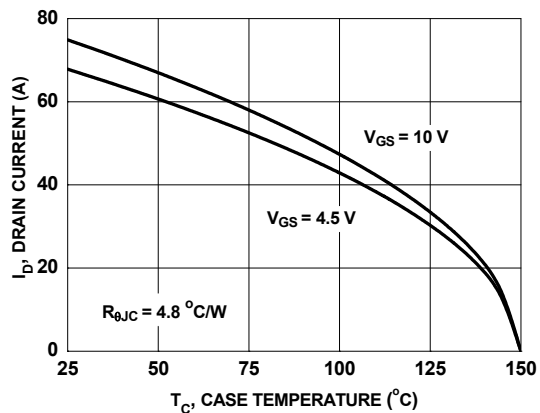


Figure 25. Maximum Continuous Drain Current vs. Case Temperature

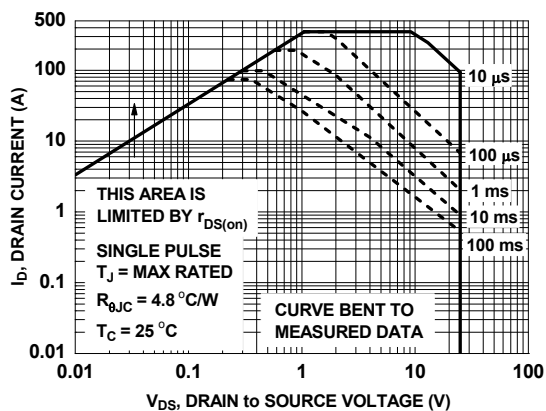


Figure 26. Forward Bias Safe Operating Area

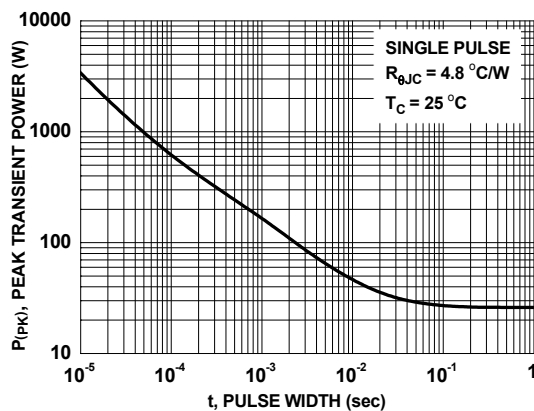
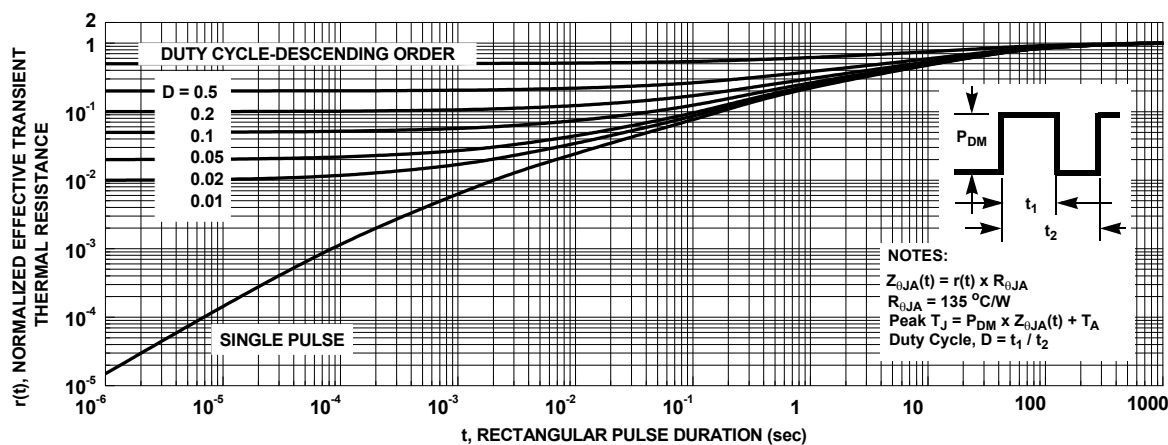
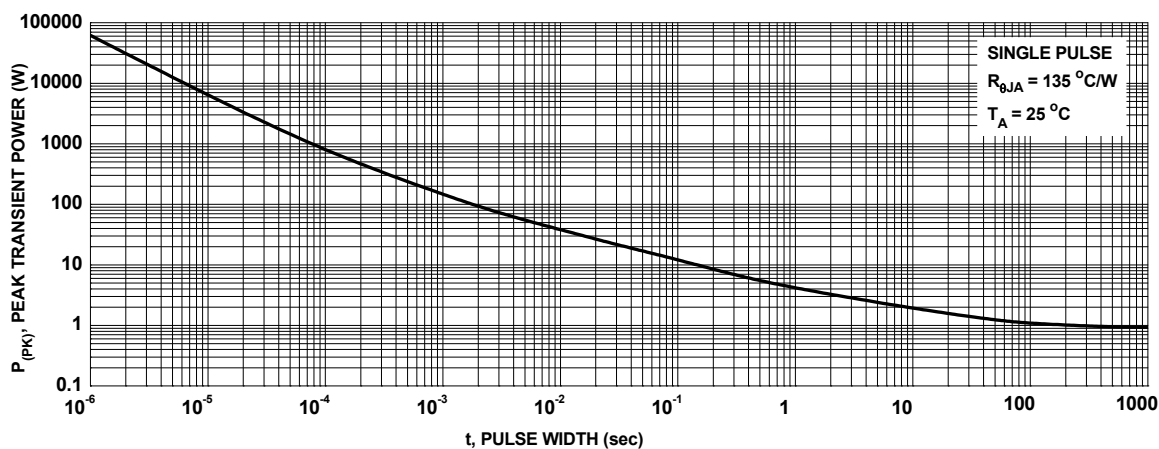
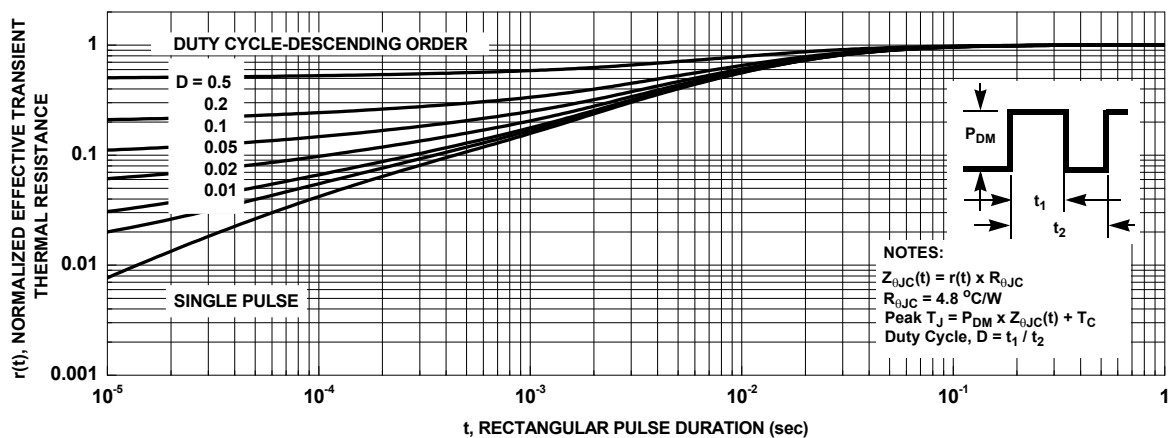
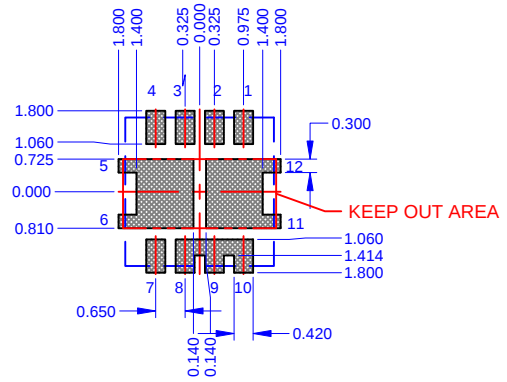


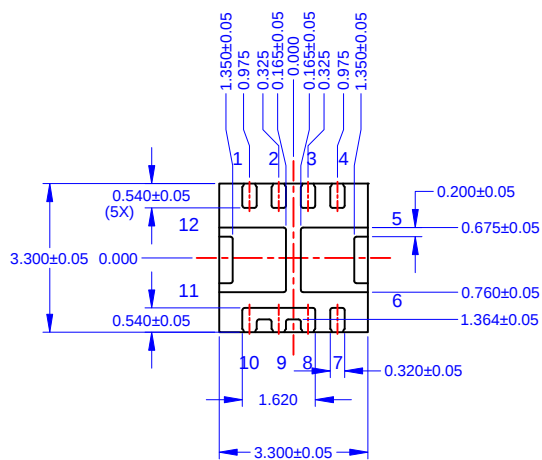
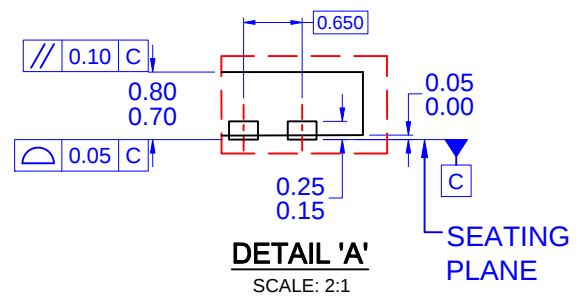
Figure 27. Single Pulse Maximum Power Dissipation

# Typical Characteristics (Q2 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.





**FRONT VIEW**  
SCALE: 1:1



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-220, VARIATION WEEC-1
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DRAWING FILE NAME: MKT-PQFN12A\_REV1



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